

SEMITOP[®]4

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SK 50 DGDL 126 T

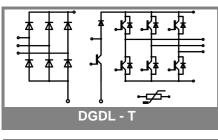
Preliminary Data

Features

- One screw mounting module
- Fully compatible with SEMITOP[®]1,2,3
- Improved thermal performances
 by aluminium oxide substrate
- Trench IGBT technology
- CAL technology free-wheeling diode
- Integrated NTC temperature sensor

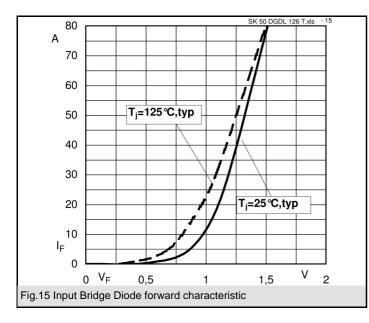
Typical Applications*

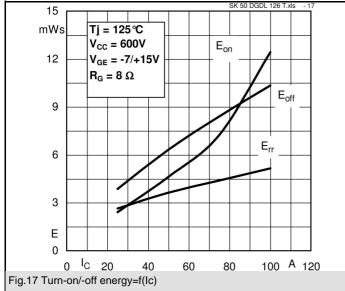
- Inverter up to 28 kVA
- Typ. motor power 15 kW
- 1) $V_{ce,sat}$, V_f = chip level value
- For IGBT chopper diagrams please refer to SK35DGDL126T

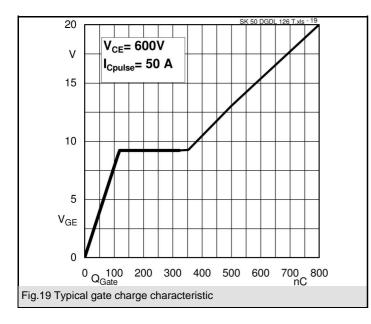


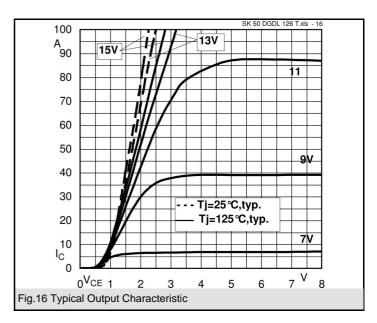
Absolute	Maximum Ratings	Ts = 25 °C, unless otherwise specified							
Symbol	Conditions	Values	Units						
IGBT - Inverter. For IGBT chopper maximum ratings, please refer to									
SK35DGDL126T									
V _{CES}		1200	V						
I _C	T _s = 25 (70) °C	68 (52)	А						
I _{CRM}	I_{CRM} = 2 x I_{Cnom} , t_p = 1 ms	100	А						
V _{GES}		± 20	V						
Т _ј		-40 +150	°C						
Diode - Inverter, Chopper									
I _F	T _s = 25 (70) °C	62 (46)	А						
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$	100	А						
Т _ј		-40 +150	°C						
Rectifier									
V _{RRM}		1600	V						
I _F	T _s = 70 °C	61	А						
I _{FSM} / I _{TSM}	t _p = 10 ms , sin 180 ° ,T _j = 25 °C	700	А						
I ² t	t _p = 10 ms , sin 180 ° ,T _j = 25 °C	2400	A²s						
T _j		-40 +150	°C						
T _{sol}	Terminals, 10 s	260	°C						
T _{stg}		-40 +125	°C						
V _{isol}	AC, 1 min. / 1 s	2500 / 3000	V						

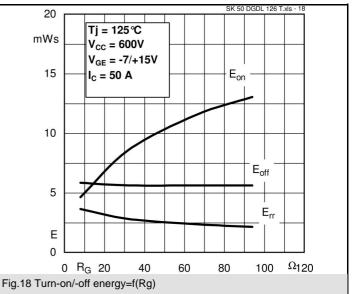
Characteristics Ts = 25 °C, unless otherwise specified							
Symbol	Conditions	min.	typ.	max.	Units		
	verter. For IGBT chopper electric	al charac	teristics,	please ref	er to		
SK35DGE							
V _{CEsat}	I _C = 50 A, T _j = 25 (125) °C		1,7 (2)	2,15 (2,45)	V		
V _{GE(th)}	$V_{GE} = V_{CE}$, $I_C = 2 \text{ mA}$	5	5,8	6,5	V		
V _{CE(TO)}	$T_{j} = 25 \ ^{\circ}C \ (125) \ ^{\circ}C$		1 (0,9)	1,2 (1,1)	V		
r _T	$T_{j} = 25 \ ^{\circ}C \ (125) \ ^{\circ}C$		14 (22)	19 (27)	mΩ		
C _{ies}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		3,7		nF		
C _{oes}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,18		nF		
C _{res}	V _{CE} = 25 V _{GE} = 0 V, f = 1 MHz		0,16		nF		
R _{th(j-s)}	per IGBT		0,6		K/W		
t _{d(on)}	under following conditions		115		ns		
t,	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$		28		ns		
t _{d(off)}	$I_{\rm C} = 50 \text{ A}, T_{\rm j} = 125 \ ^{\circ}\text{C}$		509		ns		
t _f	$R_{Gon} = R_{Goff} = 8 \Omega$		100		ns		
E _{on}	inductive load		4,6		mJ		
E _{off}			6,3		mJ		
	verter,Chopper						
V _F = V _{EC}	I _F = 50 A, T _j = 25(125) °C		1,35 (1,35)		V		
V _(TO)	T _j = 25 °C (125) °C		0,95 (0,85)		V		
r _T	$T_{j} = 25 \ ^{\circ}C \ (125) \ ^{\circ}C$		8 (10)		mΩ		
R _{th(j-s)}	per diode		1		K/W		
I _{RRM}	under following conditions		30		A		
Q _{rr}	I _F = 50 A, V _R = 600 V		10		μC		
E _{rr}	V _{GE} = 0 V, T _j = 125 °C		3,6		mJ		
	di _{F/dt} = 500 A/µs						
Diode - R	ectifier						
V _F	I _F = 35 A, T _i = 25() °C		1,1		V		
V _(TO)	T _i = 150 °C		0,8		V		
r _T	T _i = 150 °C		mΩ				
R _{th(j-s)}	per diode		K/W				
	ur sensor	1					
R _{ts}	5 %, T _r = 25 (100) °C		Ω				
Mechanic	al data						
w			60		g		
M _s	Mounting torque	2,5		2,75	Nm		
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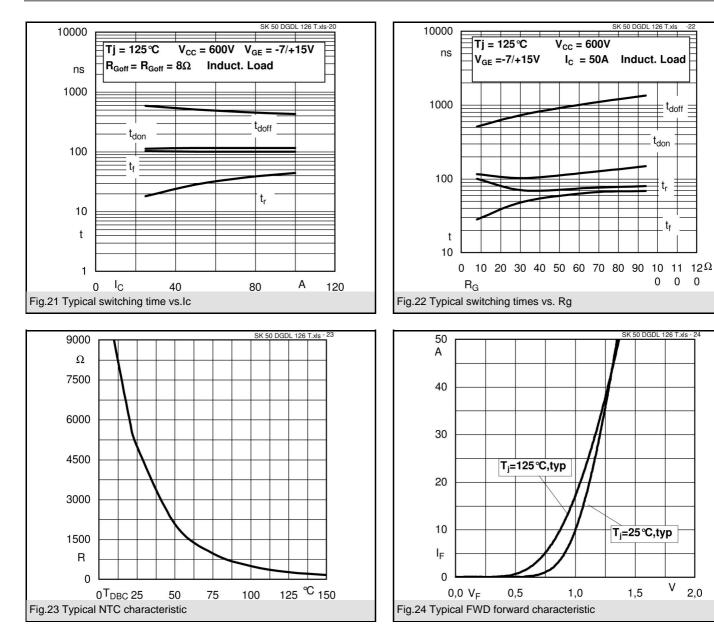








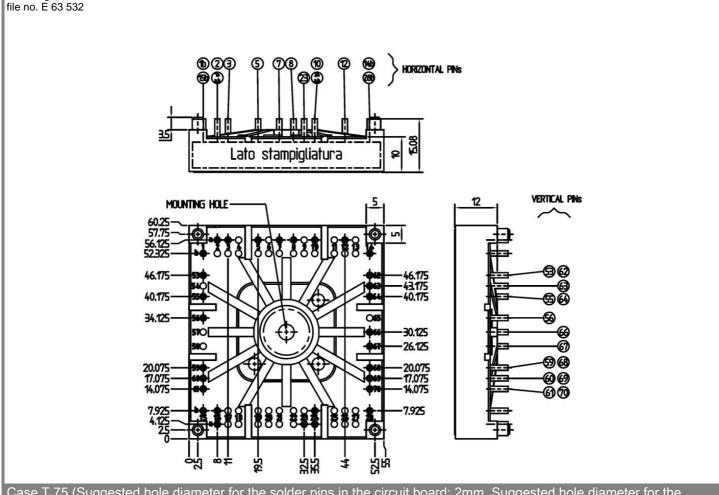


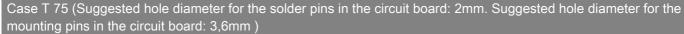


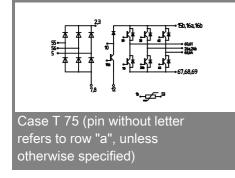
3

UL recognized

Dimensions in mm







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.